

Silicon NPN Power Transistors

2SD1451

DESCRIPTION

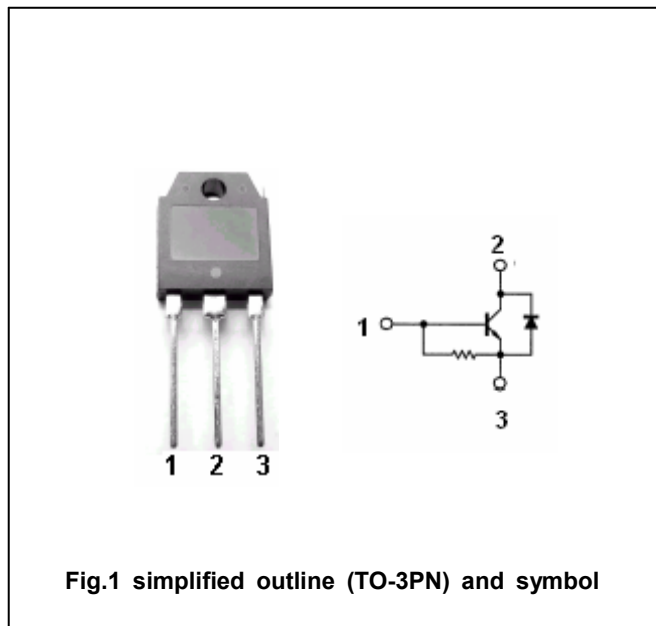
- With TO-3PN package
- High voltage,high speed
- Built-in damper diode

APPLICATIONS

- For TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		1.5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-45~150	℃

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=200mA$; $I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=1.2A$; $I_B=0.3A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=1.2A$; $I_B=0.3A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=1500V$; $I_E=0$			0.5	mA
h_{FE}	DC current gain	$I_C=0.3A$; $V_{CE}=5V$	6			
V_F	Diode forward voltage	$I_F=1.5A$			2.2	V

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[illegible]